

SLA40000 Series

High Density Gate Array

- Super-high-density/speed gate array
- Operates on 3.3 and 3.0V power source (level shifter is pre-installed)
- Raw of gates: 28 to 411k gates (sea of gates)

OVERVIEW

The SLA 40000 series are super-high-density/speed, Sea-of-gate type CMOS gate arrays adopting the 0.45 μ m process.

They consume less electricity, a feature of ASICs dedicated to 3.3V, while enabling high-speed-operation as well as 3V/5V full swing I/F in the level shifter.

There are 2- and 3-metal layer for each of 8 models from 28,260 to 411,257 gates, satisfying customer needs for a wide range of circuit size.

In addition, the series can be used with various I/F devices such as low noise output cells, PCI I/F revision 2.0, GTL I/F*, JTAG*, fail/safe output* and test control input*, and have diverse applications such as small information instrument and for image processing.

To develop high-speed/high-density circuits in a shorter period of time, the series enable diverse design techniques to be used during development such as high accuracy simulation of interconnection resistance and blunted waveform in addition to the conventional interconnection capacity components, and provide a new layout tool for reducing clock skew.

FEATURES

- Super-high density (adopting 0.45 μ m silicon gate CMOS with 2- and 3-metal layers)
- High-speed operation (operation delay of internal gate = 0.160ns at 3.3V, 2-input power NAND standard)
- Internal gate = 3.3 and 3.0V (2.0V single), I/O buffer = 5.0, 3.3 and 3.0V (2.0V single) (built-in level shifter)
- Low power consumption (0.80 μ W/MHz/BC when internal cell = 3.0V)
- Output drivability (IOL = 100 μ , 1, 3, 6, 12, 24 mA when PCI = 5.0V, IOL = 100 μ , 1, 2, 6, 12mA when PCI = 3.3V, IOL = 50 μ , 300 μ , 600 μ , 2, 4mA when 2.0V)
- RAM, PLL, IrDA*, and various function cells available
- Low noise output cell, PCI I/F, USB I/F*, LVDS*, JTAG

PRODUCT LINEUP

| Features | Master | 2-layer Metal | SLA4028 | SLA4046 | SLA4078 | SLA4115 | SLA4162 | SLA4239 | SLA4318 | SLA4411 |
|--|--|--|---------|---------|---------|---------|---------|---------|---------|---------|
| | 3-layer Metal | SLA402T | SLA404T | SLA407T | SLA411T | SLA416T | SLA423T | SLA431T | SLA441T | |
| Total BCs (Raw Gates) | | 28,260 | 46,864 | 78,600 | 115,388 | 162,864 | 239,468 | 318,308 | 411,257 | |
| Usable BCs | 2-layer Metal | 14,130 | 22,026 | 35,370 | 51,924 | 70,031 | 95,787 | 127,323 | 164,502 | |
| | 3-layer Metal | 24,868 | 39,834 | 62,880 | 86,541 | 122,148 | 167,627 | 222,815 | 287,879 | |
| Number of PADs (In Case of Micro Pitch) | | 116 | 144 | 184 | 216 | 256 | 308 | 352 | 400 | |
| | | (128) | (164) | (212) | (256) | (304) | (368) | (424) | (480) | |
| Propagation Delay | Internal Gates | tpd = 0.160ns (standard at 3.3V) | | | | | | | | |
| | Input Gates | tpd = 0.400ns (standard at 5.0V) level shifter, tpd = 0.420ns (standard at 3.3V) | | | | | | | | |
| | Output Buffers | tpd = 1.99ns (standard at 5.0V) level shifter, tpd = 1.89ns (standard at 3.3V) CL = 50pF | | | | | | | | |
| I/O Level | CMOS, TTL, PCI, USB*, LVDS* | | | | | | | | | |
| Input Mode | LVTTL, TTL, CMOS, Pull-up/Pull-down, Schmitt, 2.0/3.0/3.3/5.0V Level interface (Level shifter) | | | | | | | | | |
| Output Mode | Normal, Open drain, 3-state, Bi-directional, 2.0/3.0/3.3/5.0V Level interface (Level shifter) | | | | | | | | | |

* Under development

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